

PRELIMINARY DATA SHEET

NEC

N-CHANNEL GaAs HJ-FET NE6510379A

3 W L-BAND POWER GaAs HJ-FET

DESCRIPTION

The NE6510379A is a 3 W GaAs HJ-FET designed for middle power transmitter applications for mobile communication systems. It is capable of delivering 3 W of output power with high linear gain, high efficiency and excellent distortion.

Reliability and performance uniformity are assured by NEC's stringent quality and control procedures.

FEATURES

- GaAs HJ-FET Structure
- High Output Power : $P_o = +35$ dBm typ. @ $V_{DS} = 3.5$ V, $I_{Dset} = 200$ mA, $f = 900$ MHz, $P_{in} = +24$ dBm, 1/duty
 $P_o = +32.5$ dBm typ. @ $V_{DS} = 3.5$ V, $I_{Dset} = 200$ mA, $f = 1.9$ GHz, $P_{in} = +26$ dBm, 1/3 duty
- High Linear Gain : $G_L = 13$ dB typ. @ $V_{DS} = 3.5$ V, $I_{Dset} = 200$ mA, $f = 900$ MHz, $P_{in} = 0$ dBm, 1/3 duty
 $G_L = 8$ dB typ. @ $V_{DS} = 3.5$ V, $I_{Dset} = 200$ mA, $f = 1.9$ GHz, $P_{in} = 0$ dBm, 1/3 duty
- High Power Added Efficiency : 58% typ. @ $V_{DS} = 3.5$ V, $I_{Dset} = 200$ mA, $f = 900$ MHz, $P_{in} = +24$ dBm, 1/3 duty
52% typ. @ $V_{DS} = 3.5$ V, $I_{Dset} = 200$ mA, $f = 1.9$ GHz, $P_{in} = +26$ dBm, 1/3 duty

ORDERING INFORMATION

Part Number	Package	Supplying Form
NE6510379A-T1	79A	12 mm tape width, 1 kpcs/reel

Remark To order evaluation samples, please contact your nearby sales office.
Part number for sample order: NE6510379A

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Operation in excess of any one of these parameters may result in permanent damage.

Parameter	Symbol	Ratings	Unit
★ Drain to Source Voltage	V_{DS}	8	V
Gate to Source Voltage	V_{GS0}	-4	V
Drain Current	I_D	4.2	A
Gate Forward Current	I_{GF}	38	mA
Gate Reverse Current	I_{GR}	38	mA
Total Power Dissipation	P_T	18	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{sig}	-65 to +150	$^\circ\text{C}$

Caution Please handle this device at static-free workstation, because this is an electrostatic sensitive device.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.
Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

★ RECOMMENDED OPERATING LIMITS

Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V_{DS}			3.5	6.0	V
Gain Compression	Gcomp				3.0	dB
Channel Temperature	T_{ch}				+125	°C

ELECTRICAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$, Unless otherwise specified, using NEC standard test fixture.)

Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Saturated Drain Current	I_{DSS}	$V_{DS} = 2.5\text{ V}, V_{GS} = 0\text{ V}$		3.7		A
Pinch-off Voltage	V_p	$V_{DS} = 2.5\text{ V}, I_D = 21\text{ mA}$	-2.0		-0.4	V
Gate to Drain Break Down Voltage	BV_{gd}	$I_{gd} = 21\text{ mA}$	11			V
Thermal Resistance	R_{th}	Channel to Case		4	7	°C/W
Output Power	P_O	$f = 1.9\text{ GHz}, V_{DS} = 3.5\text{ V}$	31.5	32.5		dBm
Drain Current	I_D	$P_{in} = +26\text{ dBm}, R_g = 100\ \Omega$		760		mA
Power Added Efficiency	η_{add}	$I_{Dset} = 200\text{ mA (RF OFF)}$	44	52		%
Linear Gain ^{Note 1}	G_L	Note 2		8.0		dB

Notes 1. $P_{in} = 0\text{ dBm}$

- DC performance is 100% testing. RF performance is testing several samples per wafer. Wafer rejection criteria for standard devices is 1 reject for several samples.

TYPICAL RF PERFORMANCE FOR REFERENCE (NOT SPECIFIED)

($T_A = 25^\circ\text{C}$, Unless otherwise specified, using NEC standard test fixture.)

Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Output Power	P_O	$f = 900\text{ MHz}, V_{DS} = 3.5\text{ V}$		35.0		dBm
Drain Current	I_D	$P_{in} = +24\text{ dBm}, R_g = 100\ \Omega$		1.40		A
Power Added Efficiency	η_{add}	$I_{Dset} = 200\text{ mA (RF OFF)}$		58		%
Linear Gain ^{Note}	G_L			13.0		dB

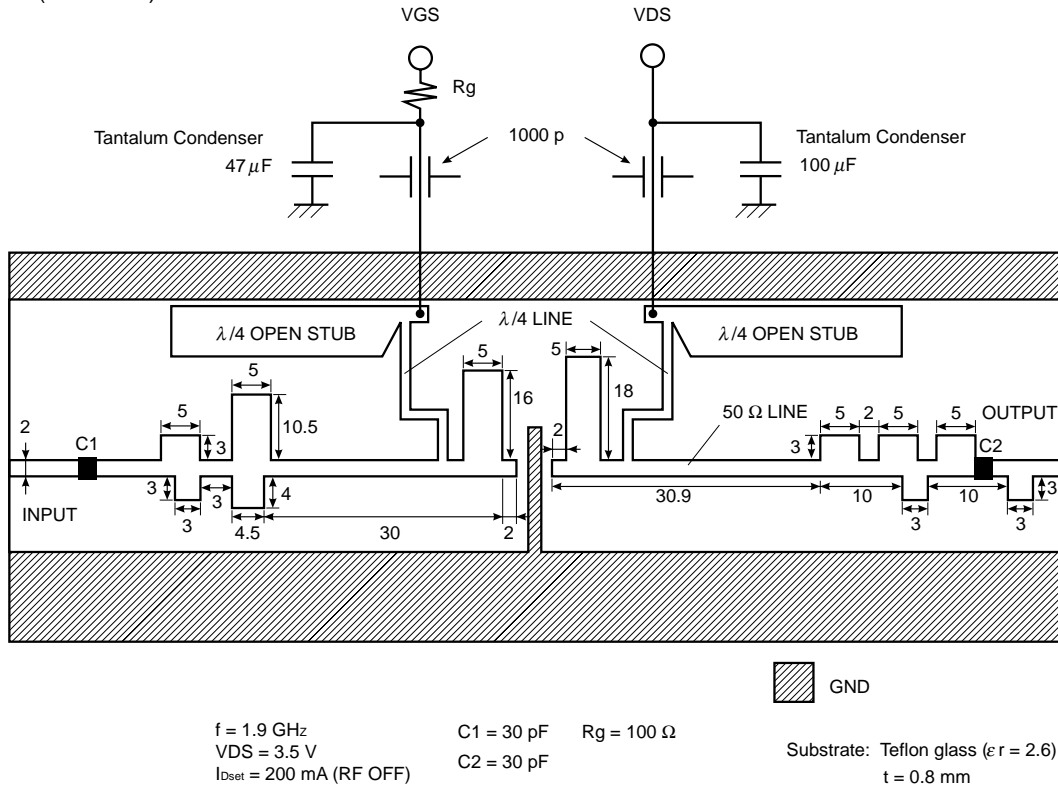
Note $P_{in} = 0\text{ dBm}$

NE6510379A S-PARAMETERS TEST CONDITIONS: $V_{DS} = 3.5\text{ V}$, $I_{Dset} = 200\text{ mA}$ (Preliminary Data)

freq. (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	MAG.	ANG. (deg.)	MAG.	ANG. (deg.)	MAG.	ANG. (deg.)	MAG.	ANG. (deg.)
600	0.958	178.7	1.601	91.9	0.017	23.4	0.848	177.3
700	0.956	178.1	1.374	91.8	0.017	26.2	0.847	176.6
800	0.954	177.1	1.210	90.7	0.017	29.7	0.845	176.1
900	0.956	176.0	1.087	90.8	0.017	33.6	0.846	175.3
1000	0.953	175.3	0.966	89.9	0.018	36.6	0.847	174.6
1100	0.952	174.4	0.869	89.7	0.018	41.0	0.848	173.8
1200	0.951	173.9	0.818	89.5	0.018	43.9	0.849	172.9
1300	0.949	173.2	0.747	88.9	0.019	45.9	0.848	172.1
1400	0.949	172.2	0.694	89.7	0.020	47.4	0.846	171.3
1500	0.952	170.6	0.656	90.0	0.020	50.2	0.846	170.4
1600	0.954	169.4	0.625	88.9	0.020	53.1	0.844	169.6
1700	0.945	168.3	0.584	90.7	0.021	56.1	0.844	168.5
1800	0.947	166.9	0.595	89.0	0.022	57.9	0.844	167.4
1900	0.949	165.0	0.570	86.1	0.022	60.3	0.846	166.1
2000	0.946	163.5	0.515	86.3	0.022	61.6	0.846	164.9
2100	0.947	161.2	0.505	85.2	0.022	64.2	0.846	163.7
2200	0.949	160.1	0.479	92.7	0.023	67.0	0.842	162.1

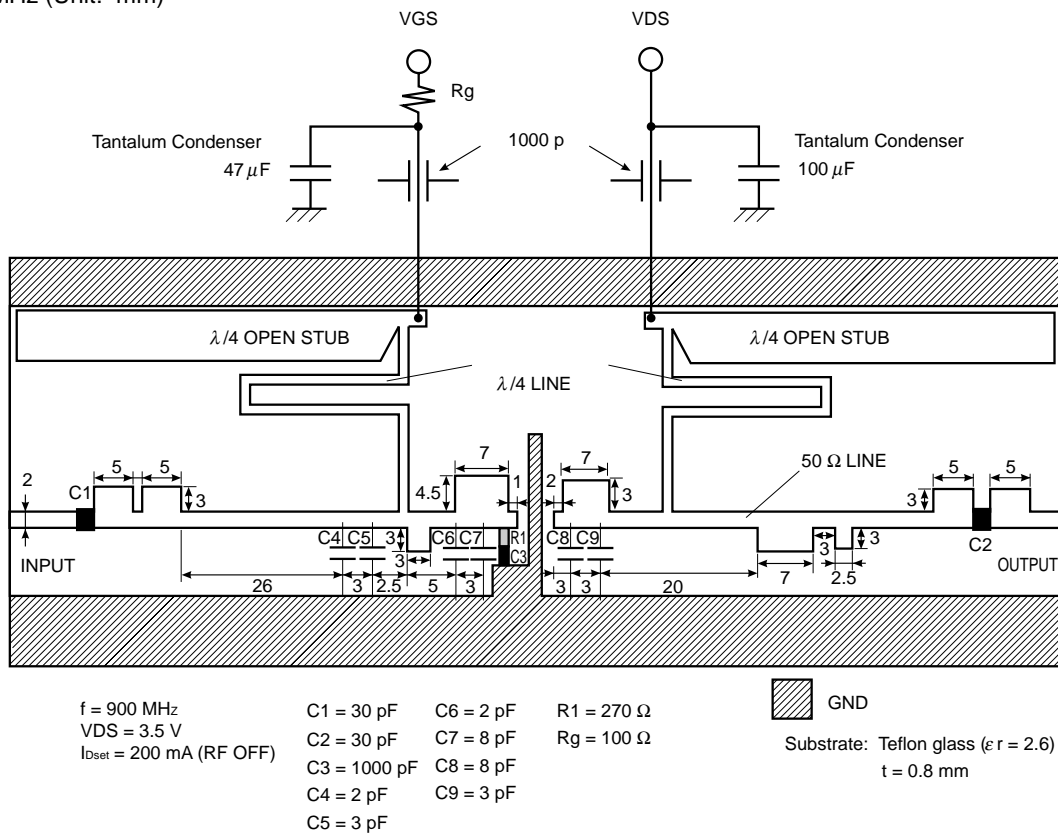
APPLICATION CIRCUIT EXAMPLE

f = 1.9 GHz (Unit: mm)

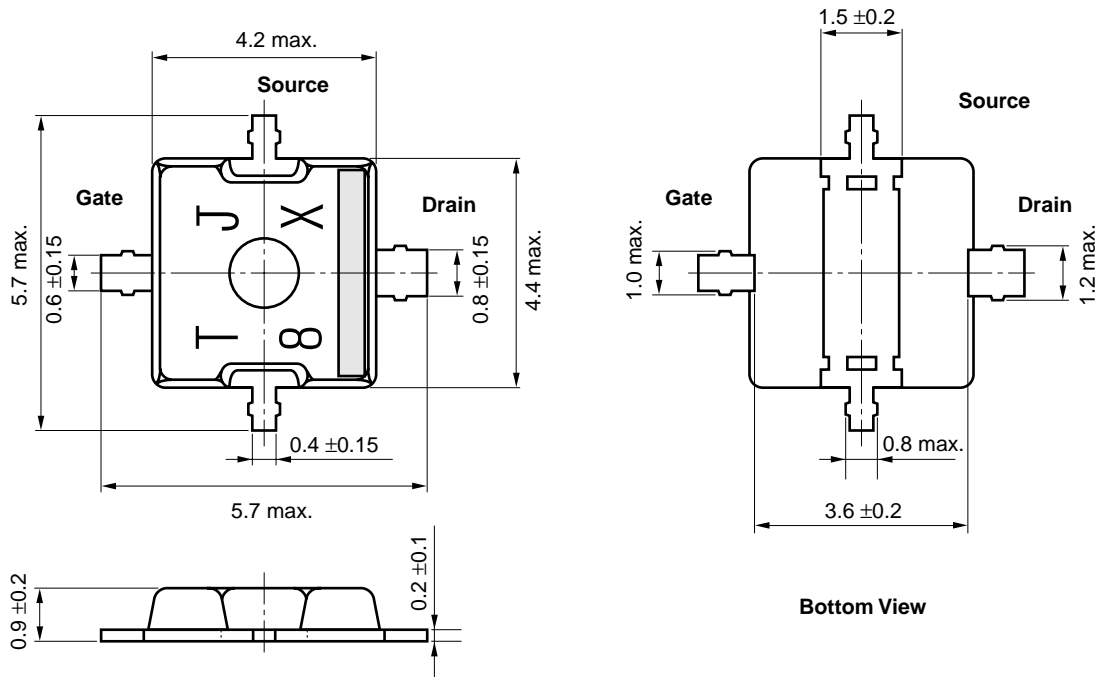


APPLICATION CIRCUIT EXAMPLE

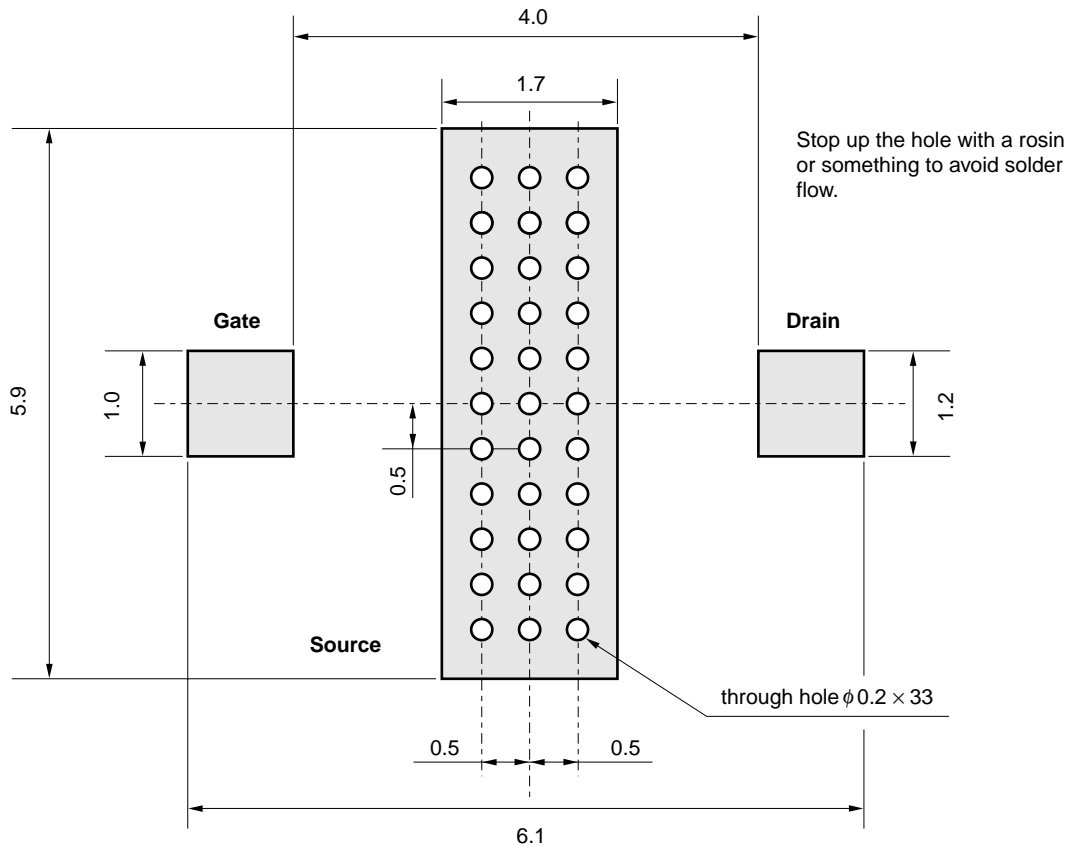
f = 900 MHz (Unit: mm)



79A Package Dimensions (Unit: mm)



79A Package Recommended P.C.B. Layout (Unit: mm)



RECOMMENDED SOLDERING CONDITIONS

This product should be soldered under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared Reflow	Package peak temperature: 235°C or below Time: 30 seconds or less (at 210°C) Count: 2, Exposure limit ^{Note} : None	IR35-00-2
Partial Heating	Pin temperature: 260°C Time: 5 seconds or less (per pin row) Exposure limit ^{Note} : None	—

Note After opening the dry pack, keep it in a place below 25°C and 65% RH for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

- **The information in this document is current as of November, 2001. The information is subject to change without notice. For actual design-in, refer to the latest publications of NEC's data sheets or data books, etc., for the most up-to-date specifications of NEC semiconductor products. Not all products and/or types are available in every country. Please check with an NEC sales representative for availability and additional information.**
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"Special": Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
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 - (2) "NEC semiconductor products" means any semiconductor product developed or manufactured by or for NEC (as defined above).

M8E 00.4-0110

SAFETY INFORMATION ON THIS PRODUCT

<p>Caution</p>	<p>GaAs Products</p>	<p>The product contains gallium arsenide, GaAs. GaAs vapor and powder are hazardous to human health if inhaled or ingested.</p> <ul style="list-style-type: none"> • Do not destroy or burn the product. • Do not cut or cleave off any part of the product. • Do not crush or chemically dissolve the product. • Do not put the product in the mouth. <p>Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.</p>
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► **Business issue**

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